

KSP2907A

General Purpose Transistor

- Collector-Emitter Voltage: V_{CEO}= 60V
 Collector Power Dissipation: P_C (max)=625mW
 Refer to KSP2907 for graphs



PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings Ta=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-60	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current	-600	mA
Pc	Collector Power Dissipation	625	mW
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 ~ 150	°C

Electrical Characteristics T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{CBO}	Collector-Base Breakdown Voltage	$I_{C} = -10 \mu A, I_{E} = 0$	-60			V
BV _{CEO}	* Collector Emitter Breakdown Voltage	I _C = -10mA, I _B =0	-60			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -10\mu A, I_C = 0$	-5			V
I _{CBO}	Collector Cut-off Current	V _{CB} = -50V, I _E =0			-10	nA
h _{FE}	DC Current Gain	$\begin{split} &I_{C}\text{=-}0.1\text{mA},\ V_{CE}\text{=-}10\text{V}\\ &V_{CE}\text{=-}10\text{V},\ I_{C}\text{=-}1\text{mA},\\ &V_{CE}\text{=-}10\text{V},\ I_{C}\text{=-}10\text{mA}\\ &V_{CE}\text{=-}10\text{V},\ ^{*}I_{C}\text{=-}150\text{mA}\\ &V_{CE}\text{=-}10\text{V},\ ^{*}I_{C}\text{=-}500\text{mA} \end{split}$	75 100 100 100 50	田	300	ic.c
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA	YE:	MA	-0.4 -1.6	V
V _{BE} (sat)	Base Emitter Saturation Voltage	I _C = -150mA, I _B = -15mA I _C = -500mA, I _B = -50mA			-1.3 -2.6	V V
C _{ob}	Output Capacitance	V _{CB} = -10V, I _E =0 f=1MHz			8	pF
f _T	* Current Gain Bandwidth Product	I _C = -50mA, V _{CE} = -20V f=100MHz	200			MHz
t _{ON}	Turn On Time	V_{CC} = -30V, I_{C} = -150mA I_{B1} = -15mA			45	ns
t _{OFF}	Turn Off Time	V_{CC} = -6V, I_{C} = -150mA I_{B1} = I_{B2} = -15mA			100	ns

^{*} Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

^{*} Also available as and PN2907

Typical Characteristics

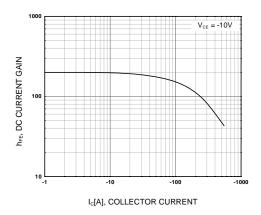


Figure 1. DC current Gain

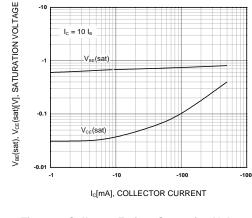


Figure 2. Collector-Emitter Saturation Voltage Base-Emitter Saturation Voltage

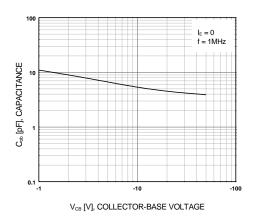


Figure 3. Output Capacitance

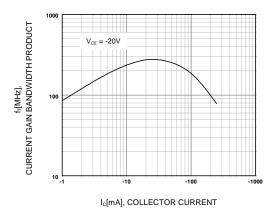
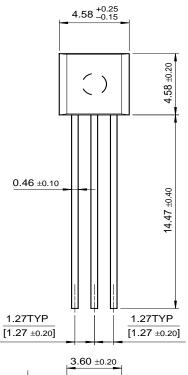


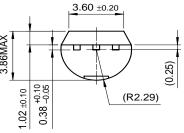
Figure 4. Current Gain Bandwidth Product

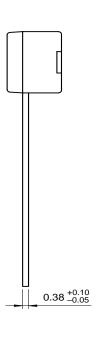
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Package Demensions

TO-92







Dimensions in Millimeters

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